

METHOD OF FORMING A THIN FILM TRANSISTOR BY UTILIZING A LASER CRYSTALLIZATION PROCESS

Abstract

An amorphous silicon pattern is formed first. A first region, a second region, at least one first pointed region adjacent to the second region and having a second height, at least one fourth region between the first region and each first pointed region are included in the amorphous silicon pattern. Each fourth region has a fourth height smaller than the second height. A laser crystallization process is performed to form a first single crystal silicon grain in each fourth region.